

- High speed ($t_f = 100\text{ns}$ typ).
- High breakdown voltage ($V_{\text{CBO}} = 1500\text{V}$).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.

Collector-to-Base Voltage	V_{CBO}	1500	V
Collector-to-Emitter Voltage	V_{CEO}	800	V
Emitter-to-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	6	A
Collector Current (Pulse)	I_{CP}	16	A
Collector Dissipation	P_C	3.0	W
	$T_c = 25^\circ\text{C}$	60	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

		min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=800V, I_E=0$		10	μA
Collector Cutoff Current	I_{CES}	$V_{CE}=1500V, R_{BE}=0$		1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C=100mA, I_B=0$	800		V
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4V, I_C=0$		1.0	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=4A, I_B=1A$		5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=4A, I_B=1A$		1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=1.0A$	8		
	$h_{FE(2)}$	$V_{CE}=5V, I_C=4A$	4	8	
Storage Time	t_{stg}	$I_C=4A, I_{B1}=0.8A$		3.0	μs
Fall Time	t_f	$I_{B2}=-1.6A$	0.1	0.2	μs

The drawing shows the TO3PML transistor package with the following dimensions (in mm):

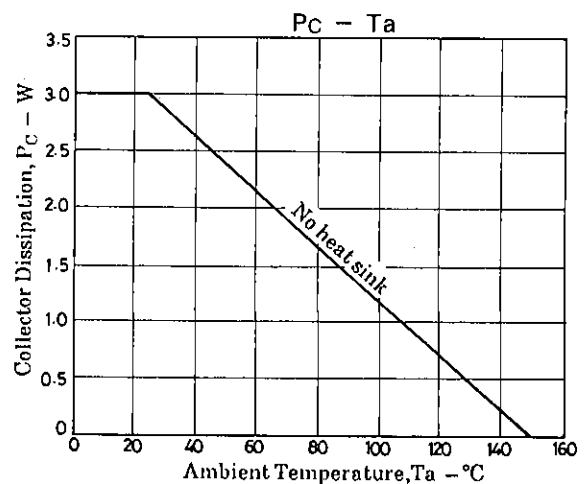
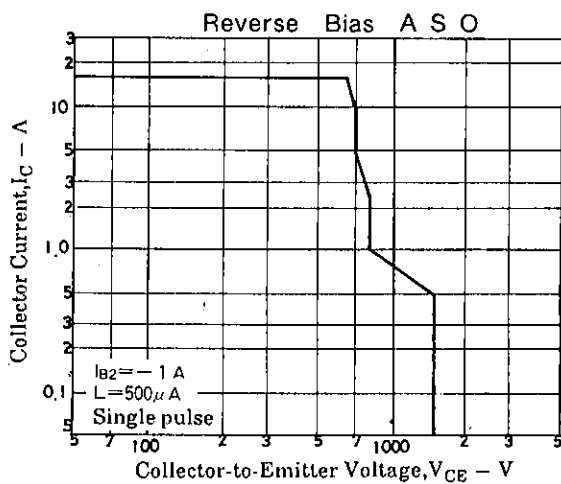
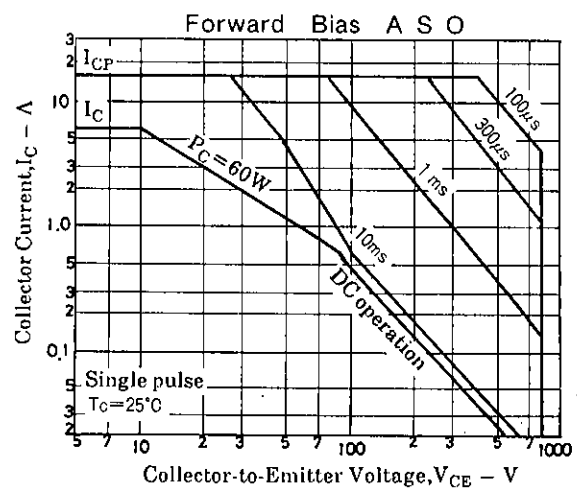
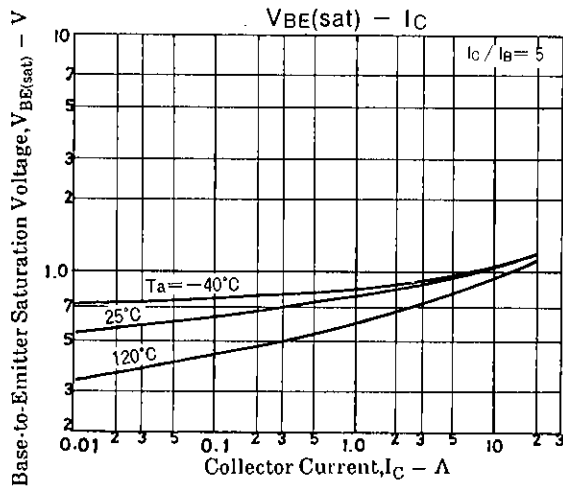
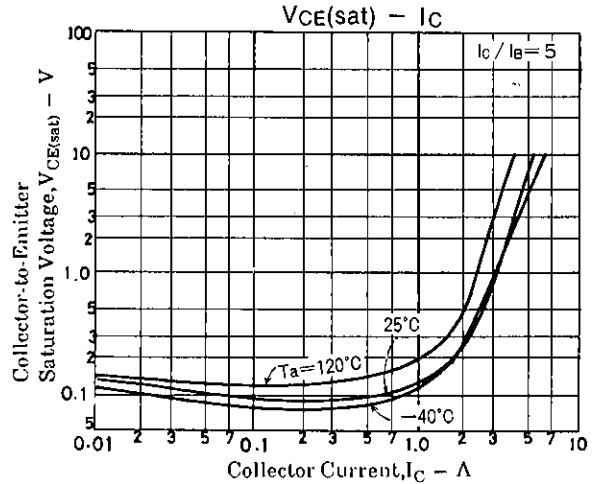
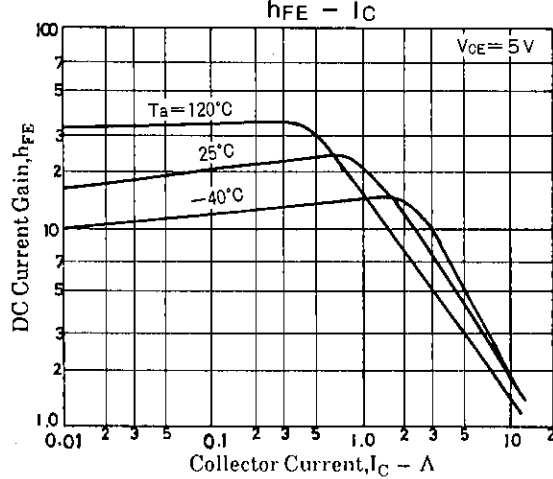
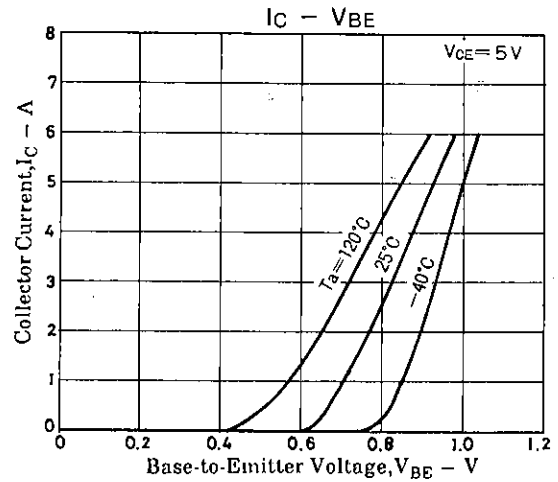
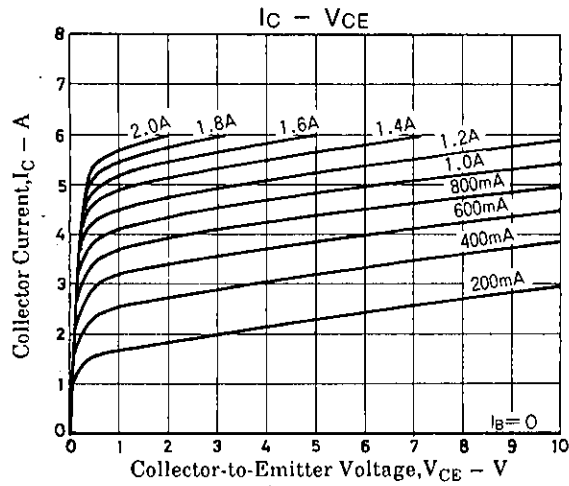
- Top View:**
 - Overall width: 22.0
 - Overall length: 20.4
 - Pin 1 diameter: 3.4
 - Pin 2 diameter: 2.8
 - Pin 3 diameter: 2.0
 - Pin 1 offset from left edge: 8.0
 - Pin 2 offset from left edge: 1.0
 - Pin 3 offset from left edge: 2.0
 - Distance between pins 1 and 2: 4.0
 - Distance between pins 2 and 3: 21.0
 - Mounting hole diameter: 5.0
 - Mounting hole offset from left edge: 16.0
- Side View:**
 - Overall height: 5.5
 - Base height: 5.45
 - Collector height: 5.45
 - Emitter height: 5.45
 - Pin 1 diameter: 3.5
- Detail View (Pin 1):**
 - Pin diameter: 5.6
 - Pin length: 3.1
 - Pin tip diameter: 0.6

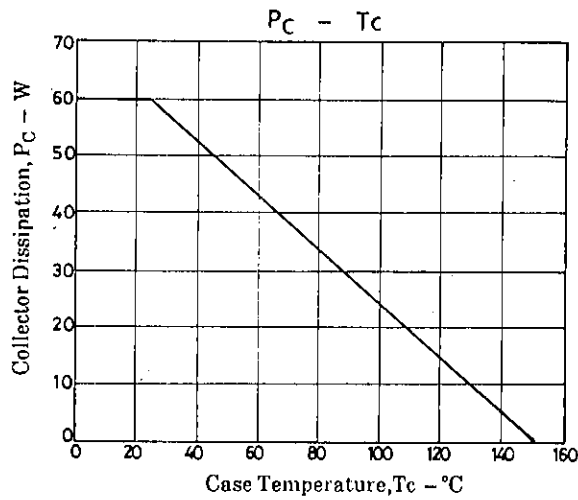
Legend:

- 1: Base
- 2: Collector
- 3: Emitter

Part Number: SANYO: TO3PML

62695TS (KOTO)/N291MH/9149MO, TS No.2965-1/3





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